



S/N 10/028643

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Kie Y. Ahn et al.	Examiner:	Long Pham
Serial No.:	10/028643	Group Art Unit:	2814
Filed:	December 20, 2001	Docket:	1303.030US1
Title:	LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO ₃ GATE DIELECTRICS		

INFORMATION DISCLOSURE STATEMENT

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In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

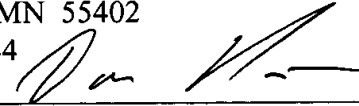
Respectfully submitted,

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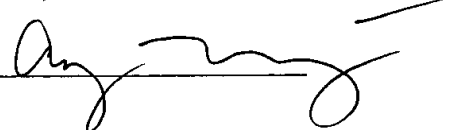
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	Application Number	10/028643
	Filing Date	December 20, 2001
	First Named Inventor	Ahn, Kie
	Group Art Unit	2814
	Examiner Name	Pham, Long
Sheet 1 of 6	Attorney Docket No: 1303.030US1	

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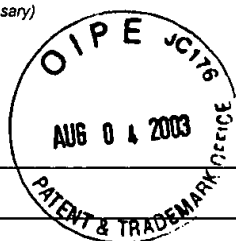
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Sheet 2 of 6

Attorney Docket No: 1303.030US1

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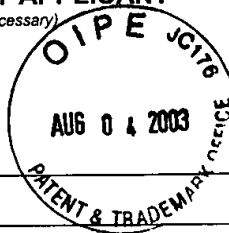
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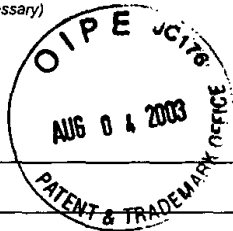
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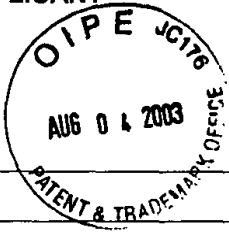
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